BIRLA INSTITUTE OF TECHNOLOGY, MESRA, RANCHI (END SEMESTER EXAMINATION)

CLASS: M.Tech. + Pre-PhD

SEMESTER: SP-22 SESSION: SP/22

BRANCH: ECE

SUBJECT: EC576 Micro-Electro-Mechanical-Systems

TIME:02 Hrs FULL MARKS: 50 INSTRUCTIONS: 1. The guestion paper contains 5 guestions each of 10 marks and total 50 marks. 2. Attempt all guestions. 3. The missing data, if any, may be assumed suitably. 4. Before attempting the question paper, be sure that you have got the correct question paper. 5. Tables/Data hand book/Graph paper etc. to be supplied to the candidates in the examination hall. _____ Q.1(a) State the intrinsic characteristics of MEMS. [2] Q.1(b) Construct an integrated accelerometer and state the operating principle. [3] Q.1(c) Illustrate the processes for development of a silicon based micromachined pressure sensor with necessary flow diagrams. [5] Explain the thermal bimorph principle. Q.2(a) [2] Ī3] Q.2(b) State the fundamentals of thermal transfer along with the governing equation of heat transfer rate for each possible mechanism. Starting from the governing equation of a mass-spring-damper system, find out the response of a MEMS [5] Q.2(c) body under sinusoidal input. Comment on bandwidth and resonant frequency. Q.3(a) Design a MEMS actuator using piezoresistor. [2] Q.3(b) Derive the expression for the pull-in-voltage of a parallel plate capacitor. [3] Describe mathematically piezoelectric effect with the help of schematic illustration of piezoelectric Q.3(c) [5] Crystal. Q.4(a) Explain tunnelling sensing. [2] Describe measurement of displacement in an accelerometer using optical Interferometry. Q.4(b) [3] A fixed-free cantilever is made of single crystal silicon. The longitudinal axis of the cantilever points in [5] Q.4(c) the [100] crystal orientation. The resistor is made by diffusion doping, with a longitudinal gauge factor of 75. The length (l), width (w), and thickness (t) of the cantilever are 500 μ m, 50 μ m and 10 μ m respectively. If a force $F = 150 \mu N$ is applied at the end of the cantilever in the longitudinal direction, what would be the percentage change of resistance? Q.5(a) Compare and contrast various bonding techniques. [2] For <100> silicon crystal, define the relation between resistivity and stress expressed in a matrix Q.5(b) [3] equation format. Q.5(c) Describe integration options of micromechanical components with integrated circuits. [5]

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